

SOT-23 Formed SMD Package

BCW89

SILICON PLANAR EPITAXIAL TRANSISTORS

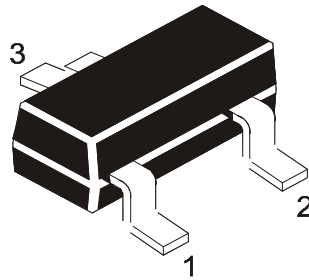
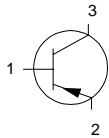
P-N-P transistors

Marking

BCW89 = H3

Pin configuration

- 1 = BASE
- 2 = EMITTER
- 3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)
 Collector-emitter voltage (open base)
 Collector current (peak value)
 Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$
 Junction temperature
 D.C. current gain at $T_j = 25\text{ }^{\circ}\text{C}$
 $-I_C = 2\text{ mA}$; $-V_{CE} = 5\text{ V}$
 Transition frequency at $f = 35\text{ MHz}$
 $-I_C = 10\text{ mA}$; $-V_{CE} = 5\text{ V}$
 Noise figure at $R_S = 2\text{ k}\Omega$
 $-I_C = 200\text{ }\mu\text{A}$; $-V_{CE} = 5\text{ V}$;
 $f = 1\text{ kHz}$; $B = 200\text{ Hz}$

$-V_{CB0}$	max.	80 V
$-V_{CE0}$	max.	60 V
$-I_{CM}$	max.	200 mA
P_{tot}	max.	250 mW
T_j	max.	150 $^{\circ}\text{C}$
	>	120
h_{FE}	<	260
f_T	typ.	150 MHz
F	<	10 dB

BCW89

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$-V_{CB0}$	max.	80 V
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	60 V
Collector-emitter voltage (open base)			
$-I_C = 2 \text{ mA}$	$-V_{CE0}$	max.	60 V
Emitter-base voltage (open collector)	$-V_{EB0}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.	150 $^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j-a}$	=	500	KW
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CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

Collector cut-off current

$I_E = 0; -V_{CB} = 20 \text{ V}$	$-I_{CB0}$	<	100 nA
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$I_E = 0; -V_{CB} = 20 \text{ V}; T_j = 100^\circ\text{C}$	$-I_{CB0}$	<	10 μA
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Base-emitter voltage

$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}; T_j = 25^\circ\text{C}$	$-V_{BE}$	600 to 750	mV
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Saturation voltages

$-I_C = 10 \text{ mA}; -I_B = 0,5 \text{ mA}$	$-V_{CEsat}$	typ.	80 mV
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		<	300 mV
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	$-V_{BEsat}$	typ.	720 mV
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$-I_C = 50 \text{ mA}; -I_B = 2,5 \text{ mA}$	$-V_{CEsat}$	typ.	150 mV
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	$-V_{BEsat}$	typ.	810 mV
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D.C. current gain

$-I_C = 10 \mu\text{A}; -V_{CE} = 5 \text{ V}$	h_{FE}	typ.	90
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$-I_C = 2 \text{ mA}; -V_{CE} = 5 \text{ V}$	h_{FE}	>	120
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		<	260
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Collector capacitance at $f = 1 \text{ MHz}$

$I_E = I_e = 0; -V_{CB} = 10 \text{ V}$	C_C	typ.	4,5 pF
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Transition frequency at $f = 35 \text{ MHz}$

$-I_C = 10 \text{ mA}; -V_{CE} = 5 \text{ V}$	f_T	typ.	150 MHz
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Noise figure at $R_S = 2 \text{ k}\Omega$

$-I_C = 200 \mu\text{A}; -V_{CE} = 5 \text{ V}$	F	<	10 dB
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$f = 1 \text{ kHz}; B = 200 \text{ Hz}$			
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Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
SOT-23 T&R	3K/reel	136 gm/3K pcs	3" x 7.5" x 7.5"	12.0K	17" x 15" x 13.5"	192.0K	12 kgs
			9" x 9" x 9"	51.0K	19" x 19" x 19"	408.0K	28 kgs
	10K/reel	415 gm/10K pcs	13" x 13" x 0.5"	10.0K	17" x 15" x 13.5"	300.0K	16 kgs

Customer Notes

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

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